

N-Channel Enhancement Mode Power MOSFET

MTN10N65EA

 $BV_{DSS} : 700V @ T_j=150^{\circ}C$ **$R_{DS(ON)} : 0.85 \Omega$** **$I_D : 10A$**

Description

The MTN10N65EA is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The SOT-82 package is universally preferred for all commercial-industrial applications

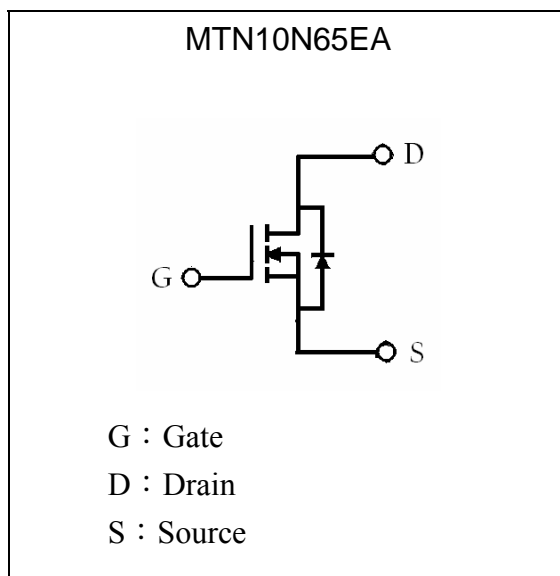
Features

- $BV_{DSS}=700V$ typically @ $T_j=150^{\circ}C$
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

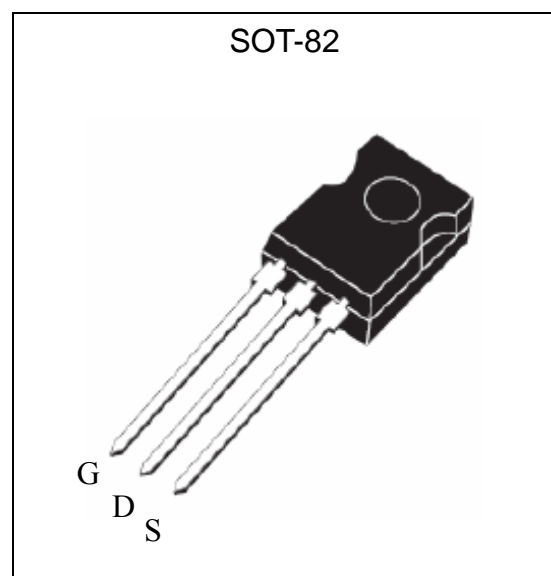
Applications

- Power Factor Correction
- LCD TV Power
- Full and Half Bridge Power

Symbol



Outline



**Absolute Maximum Ratings** ($T_C=25^{\circ}\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage (Note 1)	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	10*	A
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$	I_D	6	A
Pulsed Drain Current @ $V_{GS}=10\text{V}$ (Note 2)	I_{DM}	40*	A
Single Pulse Avalanche Energy @ $L=4.3\text{mH}$, $I_D=10\text{Amps}$, $V_{DD}=50\text{V}$	E_{AS}	237	mJ
Repetitive Avalanche Energy	E_{AR}	5	
Peak Diode Recovery dv/dt (Note 3)	dv/dt	3.0	V/ns
Maximum Temperature for Soldering @ Lead at 0.063 in(1.6mm) from case for 10 seconds	T_L	300	$^{\circ}\text{C}$
Maximum Temperature for Soldering @ Package Body for 10 seconds	T_{PKG}	260	$^{\circ}\text{C}$
Total Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_d	50	W
Linear Derating Factor		0.4	W/ $^{\circ}\text{C}$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^{\circ}\text{C}$

*Drain current limited by maximum junction temperature

- Note : 1. $T_J=+25^{\circ}\text{C}$ to $+150^{\circ}\text{C}$.
2. Repetitive rating; pulse width limited by maximum junction temperature.
3. $I_{SD}\leq 10\text{A}$, $dI/dt\leq 100\text{A}/\mu\text{s}$, $V_{DD}\leq BVDSS$, $T_J=+150^{\circ}\text{C}$.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	2.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	100	$^{\circ}\text{C}/\text{W}$



Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	650	-	-	V	V _{GS} =0, I _D =250μA
BV _{DSS}	-	700	-	V	V _{GS} =0, I _D =250μA, Tj=150°C
ΔBV _{DSS} /ΔTj	-	0.631	-	V/°C	Reference to 25°C, I _D =250μA
BV _{DS}	-	700	-	V	V _{GS} =0, I _D =10A
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	6.8	-	S	V _{DS} =15V, I _D =5A
I _{GSS}	-	-	±100	nA	V _{GS} =±30
I _{DSS}	-	-	25	μA	V _{DS} =650V, V _{GS} =0
I _{DSS}	-	-	250	μA	V _{DS} =520V, V _{GS} =0, Tj=125°C
*R _{DS(ON)}	-	0.75	0.85	Ω	V _{GS} =10V, I _D =6A
Dynamic					
*Q _g	-	39	-	nC	I _D =10A, V _{DD} =300V, V _{GS} =10V
*Q _{gs}	-	9.5	-		
*Q _{gd}	-	17.6	-		
*t _{d(ON)}	-	19	-	ns	V _{DD} =300V, I _D =10A, V _{GS} =10V, R _G =9.1 Ω
*t _r	-	16	-		
*t _{d(OFF)}	-	49	-		
*t _f	-	16	-		
C _{iss}	-	1882	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	170	-		
C _{rss}	-	20	-		
Source-Drain Diode					
*V _{SD}	-	-	1.5	V	I _S =10A, V _{GS} =0V
*I _S	-	-	10	A	V _D =V _G =0, V _S =1.3V
*I _{SM}	-	-	40		
*t _{rr}	-	352	528	ns	V _{GS} =0, I _F =10A, dI/dt=100A/μs
*Q _{rr}	-	2.9	4.35	μC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

Ordering Information

Device	Package	Shipping	Marking
MTN10N65EA	SOT-82 (RoHS compliant)	200 pcs/bag, 10 bags/box, 10 boxes / carton	10N65

Characteristic Curves

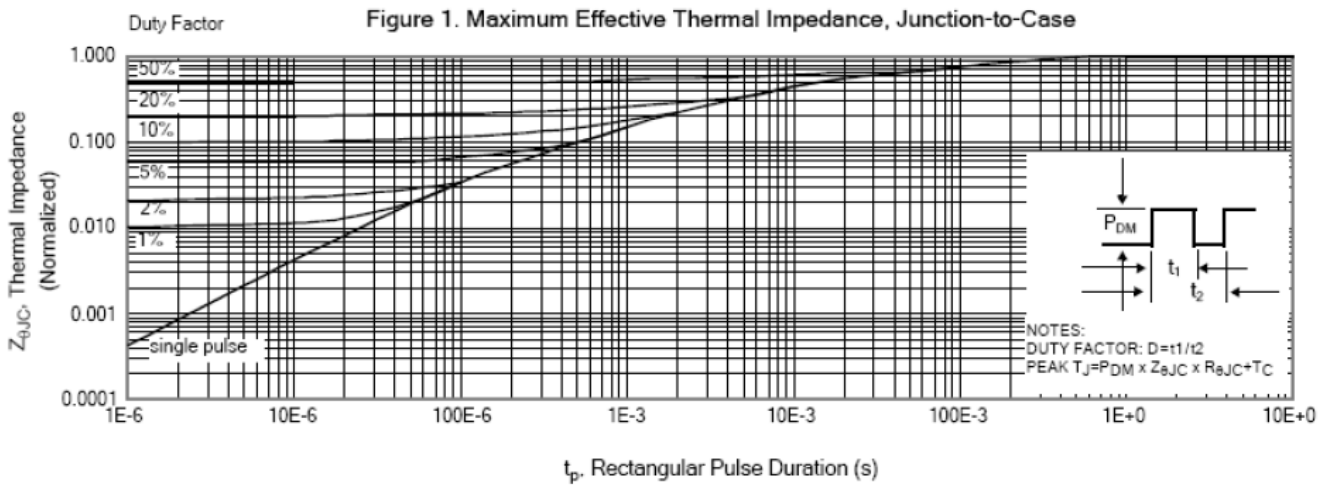


Figure 2. Maximum Power Dissipation vs Case Temperature

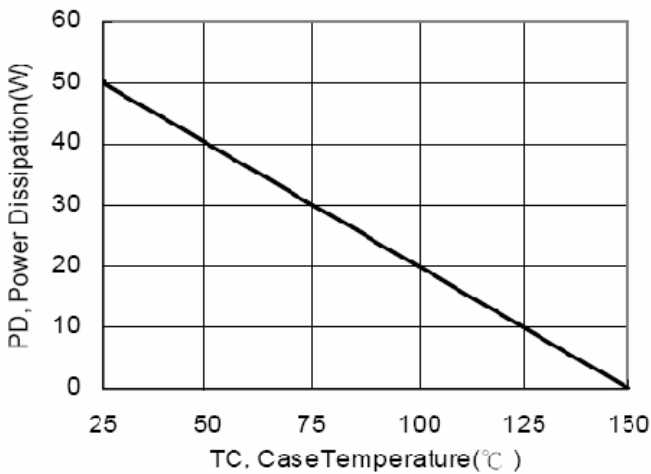


Figure 3. Maximum Continuous Drain Current vs Case Temperature

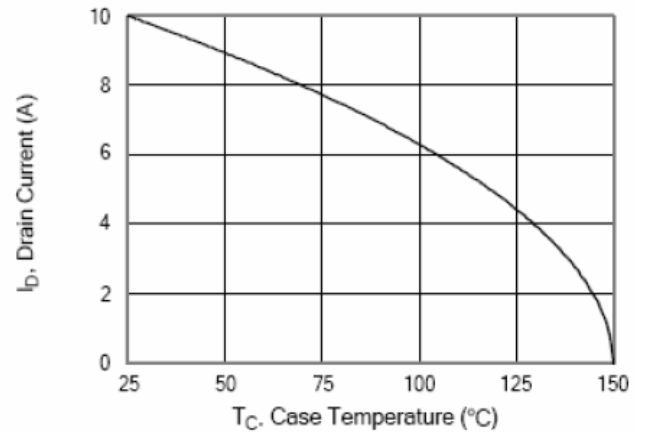


Figure 4. Typical Output Characteristics

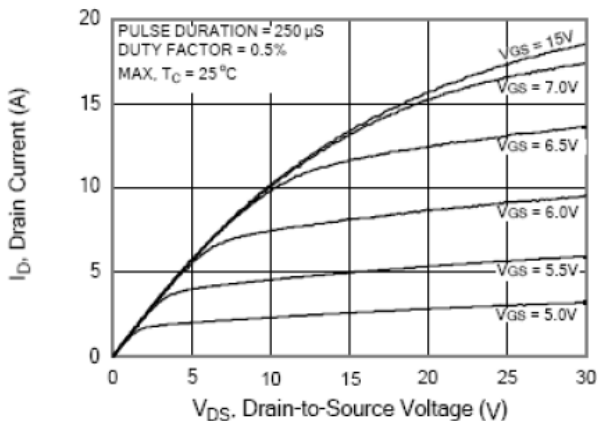
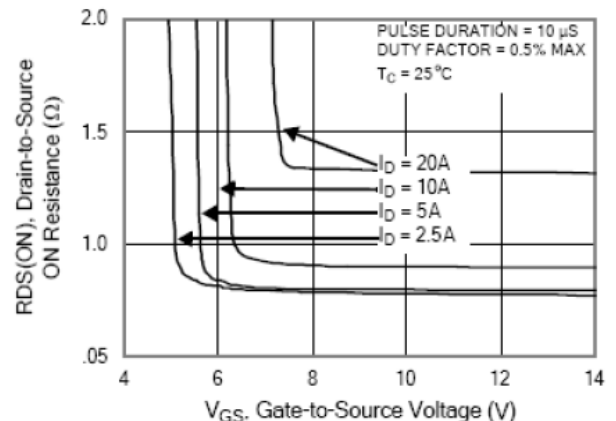


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current



Characteristic Curves(Cont.)

Figure 6. Maximum Peak Current Capability

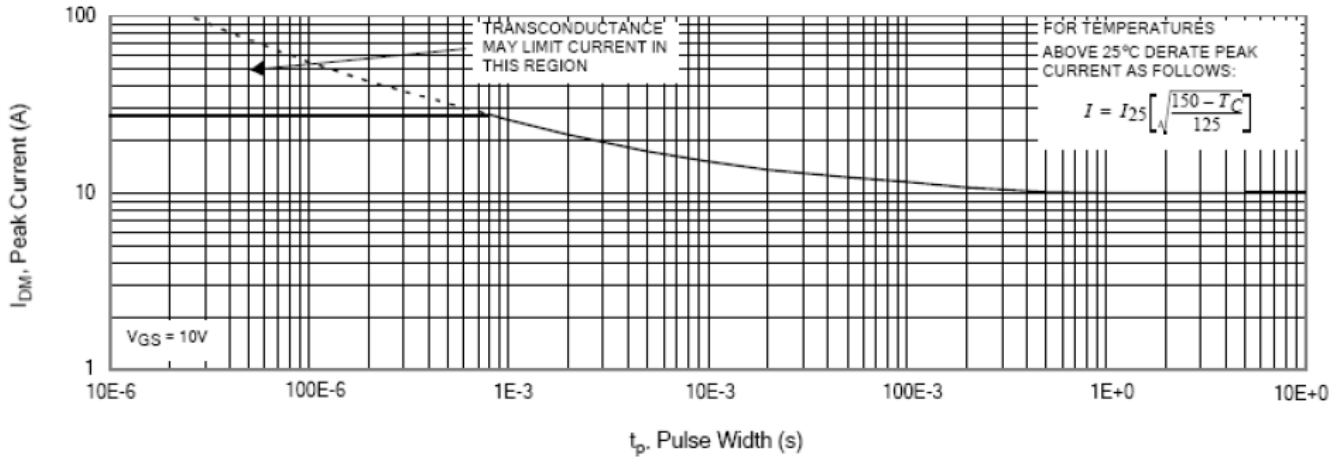


Figure 7. Typical Transfer Characteristics

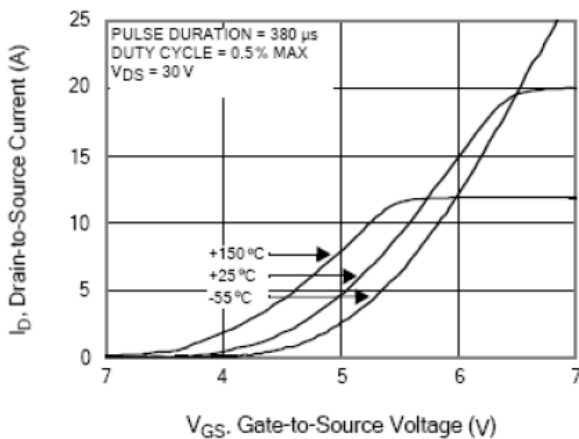


Figure 8. Unclamped Inductive Switching Capability

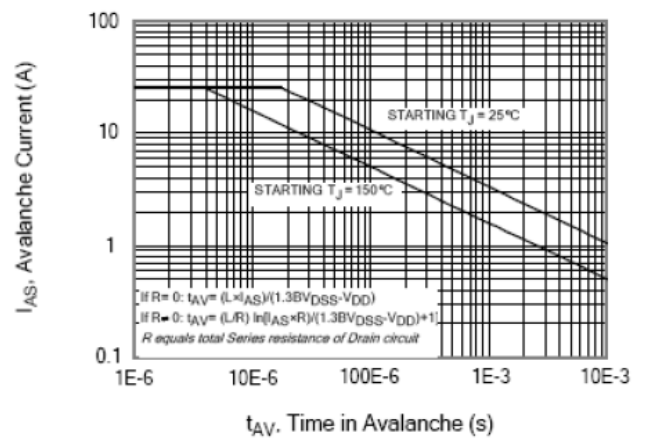


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

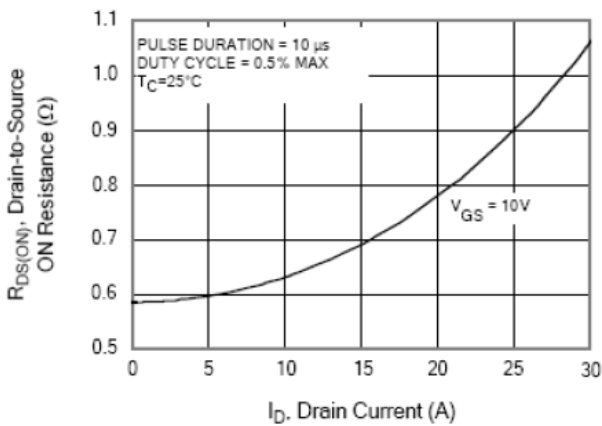
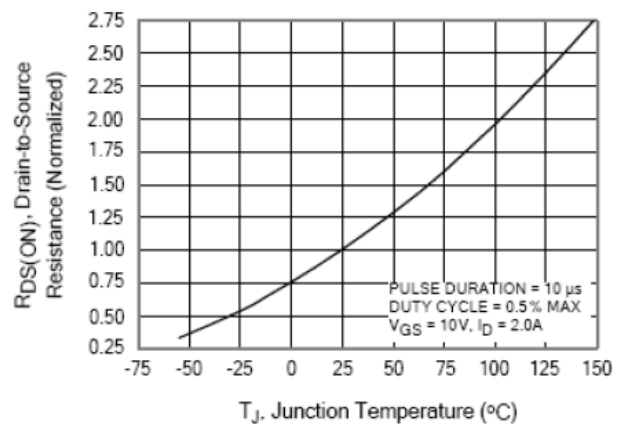


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature



Characteristic Curves(Cont.)

Figure 11. Typical Breakdown Voltage vs Junction Temperature

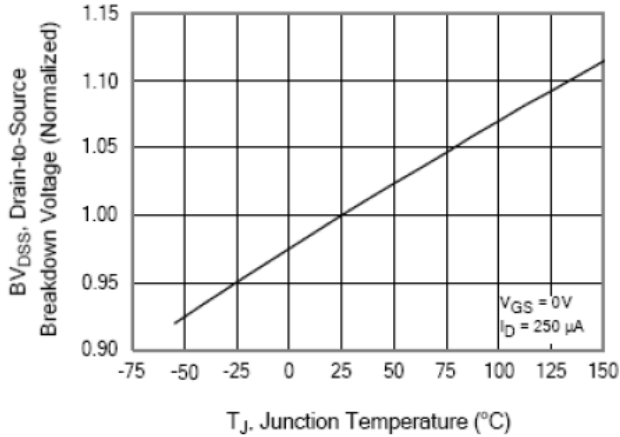


Figure 12. Typical Threshold Voltage vs Junction Temperature

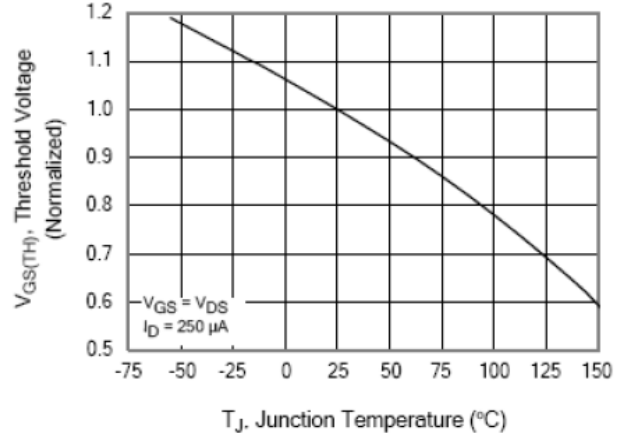


Figure 13. Maximum Forward Bias Safe Operating Area

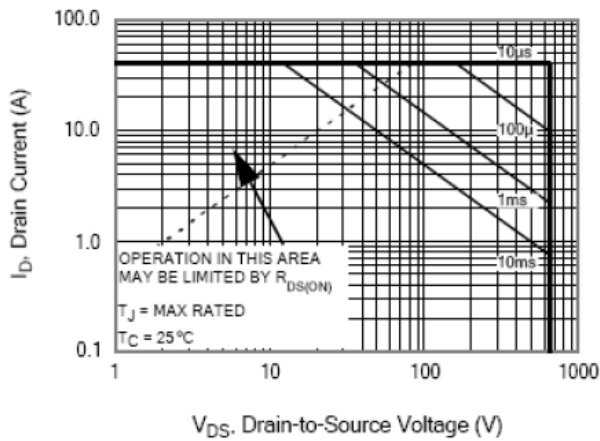


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

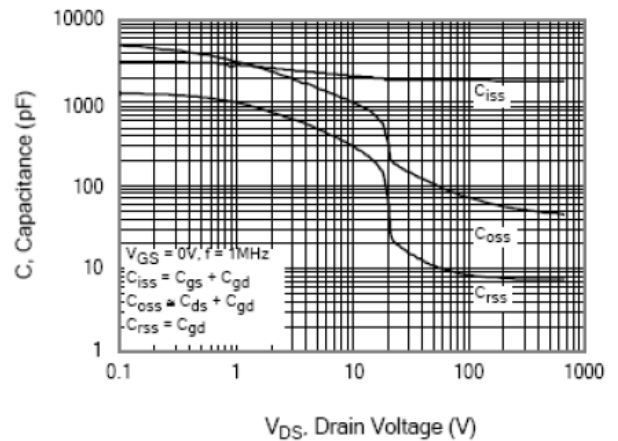


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

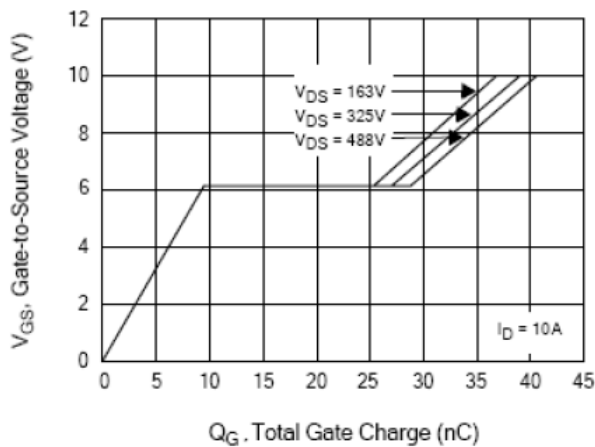
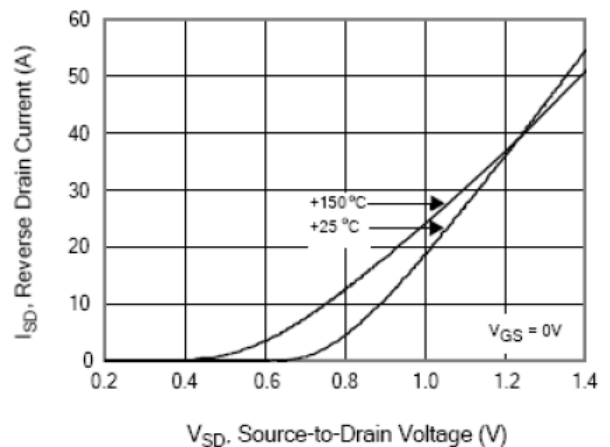


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuit and Waveforms

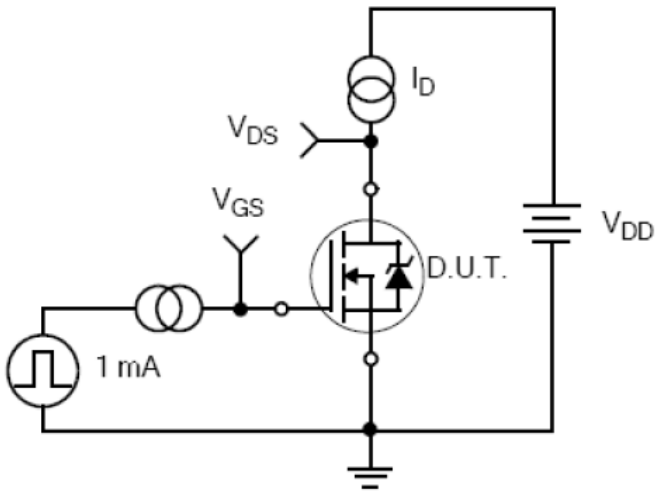


Figure 17. Gate Charge Test Circuit

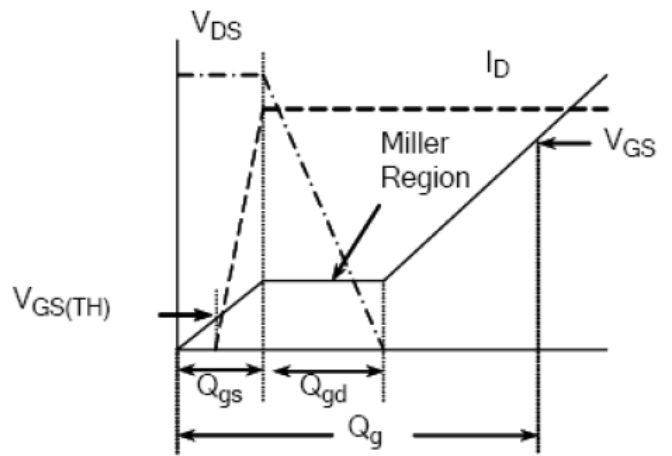


Figure 18. Gate Charge Waveform

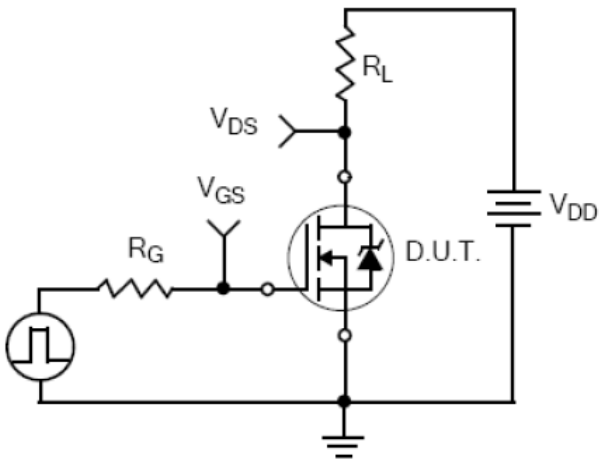


Figure 19. Resistive Switching Test Circuit

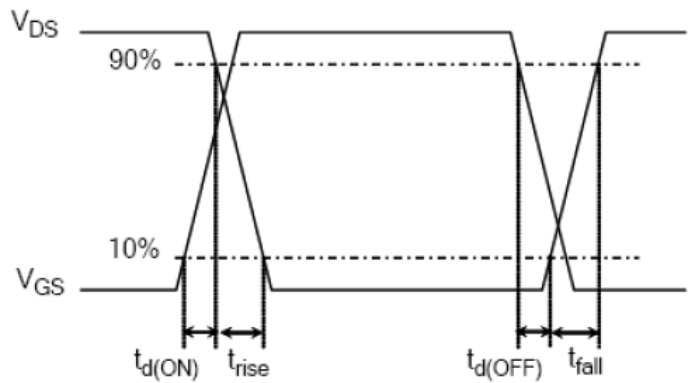


Figure 20. Resistive Switching Waveforms

Test Circuit and Waveforms(Cont.)

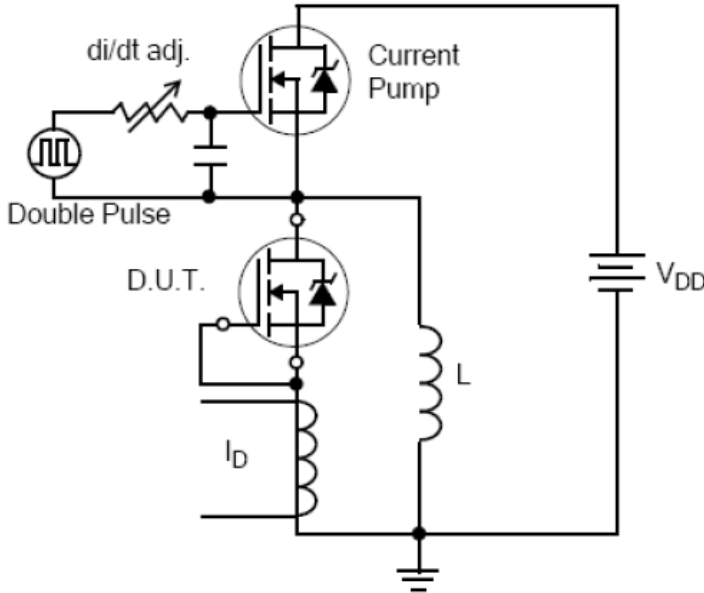


Figure 21. Diode Reverse Recovery Test Circuit

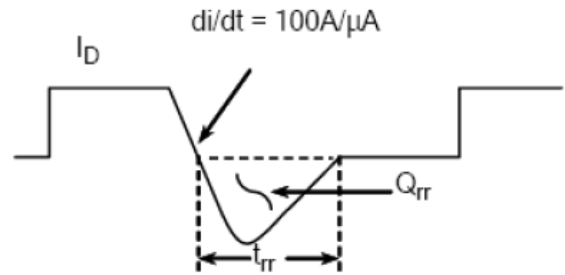


Figure 22. Diode Reverse Recovery Waveform

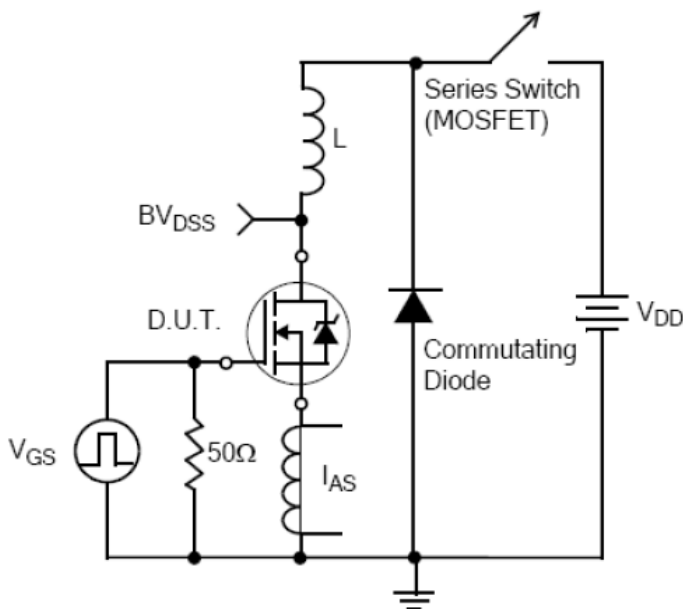


Figure 23. Unclamped Inductive Switching Test Circuit

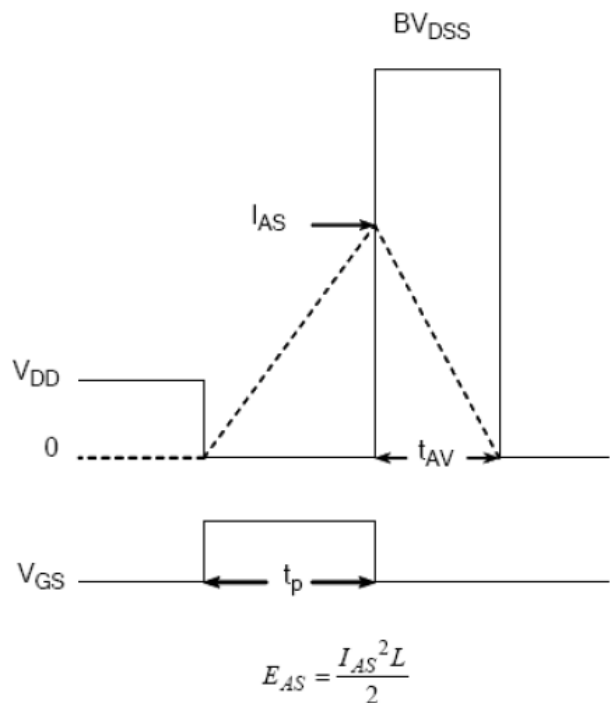
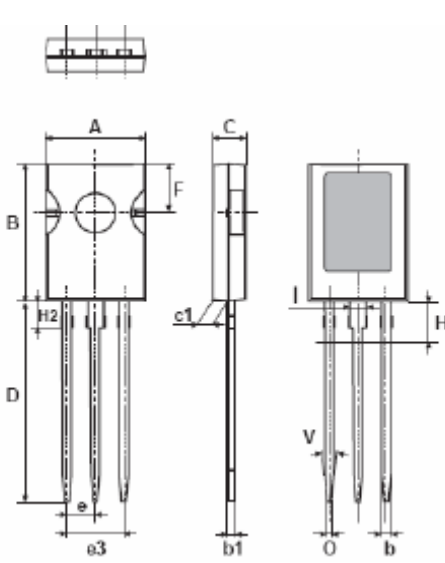


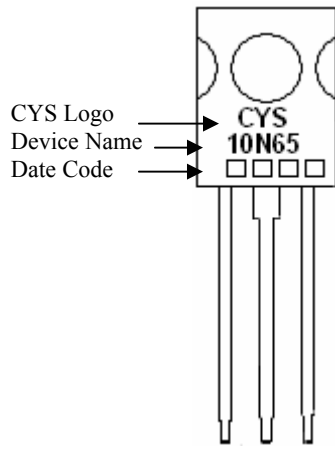
Figure 24. Unclamped Inductive Switching Waveforms

SOT- 82 Dimension



3-Lead SOT-82 Plastic Package
CYStek Package Code: EA

Marking:



Style: Pin 1.Gate 2.Drain 3.Source
4.Drain

*Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.291	0.307	7.4	7.8	e3	0.163	0.183	4.15	4.65
B	0.413	0.425	10.5	10.8	F	*0.149		*3.8	
b	0.028	0.035	0.7	0.9	H	*0.100		*2.54	
b1	0.019	0.029	0.49	0.75	H2	*0.084		*2.15	
C	0.094	0.106	2.4	2.7	I	*0.05		*1.27	
c1	0.039	0.051	1.0	1.3	O	*0.012		*0.3	
D	0.606	0.630	15.4	16.0	V	*10°		*10°	
e	*0.086		*2.2						

- Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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